

InGaAs / InP PIN Chip ---TK912P3C

1. Scope

- The specification applies to photo-diode chips for PIN-TIA.
- Type : TK912P3C

2. Structure

- InGaAs / InP PIN Chip.
- P Electrode (anode) : Gold.
- N Electrode (cathode) : Gold.

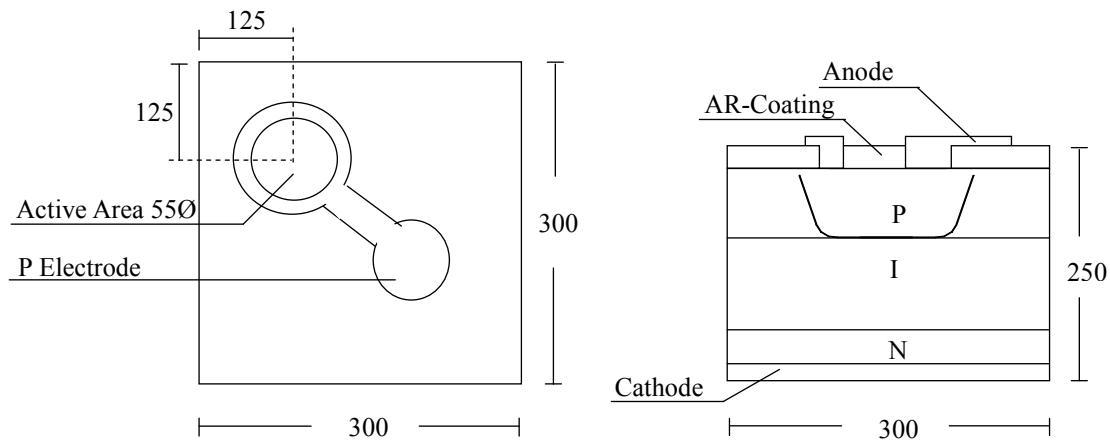
3. Size

- Chip size : 300 × 300 μ m
- Thickness : 250 ± 25 μ m
- Active area : 55 μ m (diameter)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(T_a = +25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Responsivity	R	V _r =5V, λ =1300nm	0.9	0.93	*	A/W
Dark Current	I _d	V _r =5V	*	0.1	1	nA
Capacitance	C	V _r =5V, f=1MHZ	*	0.55	0.75	pF



Unit : μ m

fig. 1

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